CE3110 - Electronic Devices Laboratory

**CE 3110** Electronic Devices Laboratory (1 semester credit hour) Laboratory to accompany **CE 3310**. Experimental determination and illustration of properties of carriers in semiconductors including carrier drift, carrier diffusion; p-n junctions including forward and reverse bias effects and transient effects; bipolar transistors including the Ebers-Moll model and secondary effects; field effect transistors including biasing effects, MOS capacitance and threshold voltage. Corequisite: **CE 3310** or **EE 3310**. Prerequisite: **RHE T 1302**. (Same as **EE 3110**) (0-3) S